

REMARKS

Claim 41 is added herein and claim 35 is cancelled. Claims 1-2 are pending and under consideration. Claims 3-40 are withdrawn from consideration.

Independent claim 1 recites the wires have a first dopant doped therein by an ion implantation process carried out to regulate an electric resistance of the wires after forming the wire/resistance heat emitting body pattern over the substrate. Thus, the wires are doped. In contrast, Taniguchi teaches doping the silicon layer 3 in different amounts to form low and high resistance regions 3A and 3B. Taniguchi, col. 5, ln. 3-16. Thus, the doping is not performed on the wires.

New claim 41 recites the resistance heat emitting bodies are undoped. In contrast, the high resistance region 3B of Taniguchi is doped to an impurity concentration of $3 \times 10^{17}/\text{cm}^3$. Taniguchi, col. 5, ln. 8.

Accordingly, withdrawal of the rejection is requested.

There being no further outstanding objections or rejections, it is submitted that the application is in condition for allowance. An early action to that effect is courteously solicited.

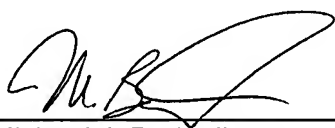
Finally, if there are any formal matters remaining after this response, the Examiner is requested to telephone the undersigned to attend to these matters.

If there are any additional fees associated with filing of this Amendment, please charge the same to our Deposit Account No. 19-3935.

Respectfully submitted,

STAAS & HALSEY LLP

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